

isc Silicon NPN Power Transistor**MJ12022****DESCRIPTION**

- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = 450V(\text{Min})$
- Fast Turn-Off Time
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

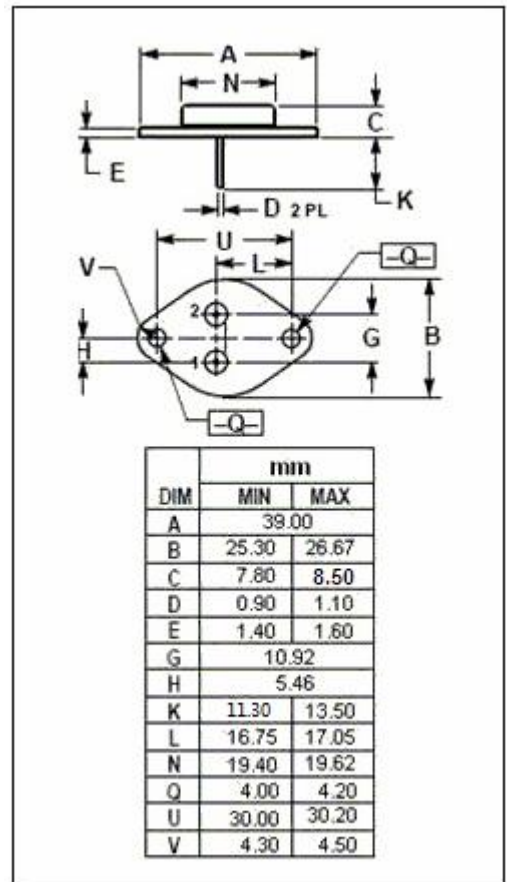
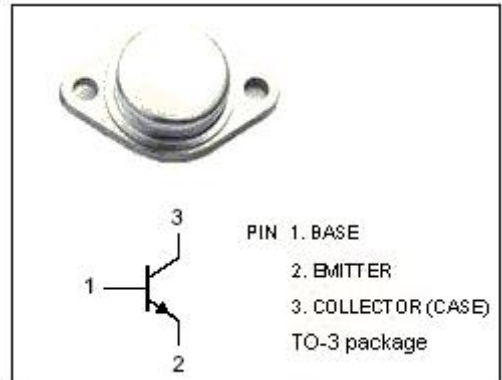
- Designed for high resolution video systems, such as : high density graphic displays, data terminals, video scanners.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector- Base Voltage	850	V
$V_{CEO(SUS)}$	Collector-Emitter Voltage	450	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	15	A
I_{CM}	Collector Current-Peak	20	A
I_B	Base Current-Continuous	10	A
I_{BM}	Base Current-Peak	15	A
P_C	Collector Power Dissipation@ $T_C=25^\circ\text{C}$	175	W
T_J	Junction Temperature	200	$^\circ\text{C}$
T_{stg}	Storage Temperature	-65~200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.0	$^\circ\text{C/W}$



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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=30\text{mA}$; $I_B=0$	450			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=10\text{A}$; $I_B=2\text{A}$			1.2	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=10\text{A}$; $I_B=2\text{A}$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=850\text{V}$; $I_E=0$ $V_{CB}=850\text{V}$; $I_E=0$; $T_C=100^{\circ}\text{C}$			0.25 1.5	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=6\text{V}$; $I_C=0$			1.0	mA
h_{FE}	DC Current Gain	$I_C=15\text{A}$; $V_{CE}=5\text{V}$	5			
f_T	Current-Gain—Bandwidth Product	$I_C=1.3\text{A}$; $V_{CE}=10\text{V}$; $f_{test}=1\text{MHz}$	15			MHz
C_{OB}	Output Capacitance	$I_E=0$; $V_{CB}=10\text{V}$; $f_{test}=1\text{kHz}$		400		pF
Switching times; Inductive Load						
t_s	Storage Time	$I_C=10\text{A}$, $V_{CC}=120\text{V}$; $I_{B1}=2\text{A}$; $PW=8\mu\text{s}$; $V_{BE(off)}=4\text{V}$ Duty Cycle $\leq 2.0\%$		820		ns
t_f	Fall Time			100		ns

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